SMD Schottky Barrier Diode

CDBF0130

Io = 100 mA
VR = 30 Volts
RoHS Device

Features

-Designed for mounting on small surface.

-Extremely thin package.

-Low stored charge.

-Majority carrier conduction.

Mechanical data

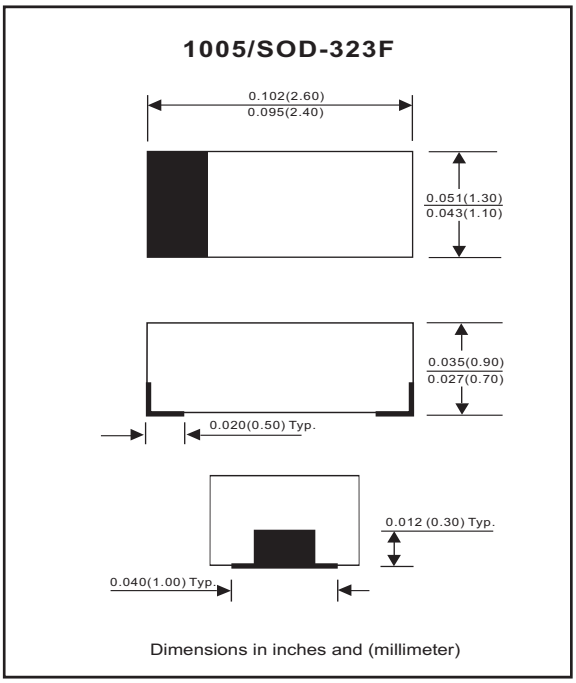
-Case: 1005/SOD-323F standard package, molded plastic.

-Terminals: Gold plated, solderable per MIL-STD-750,method 2026.

-Polarity: Indicated by cathode band.

-Mounting position: Any

-Weight: 0.006 gram(approx.).



Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		VRRM			35	V
Reverse voltage		VR			30	V
Average forward current		Io			100	mA
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load(JEDEC method)	IFSM		1000		mA
Power Dissipation		PD			250	mW
Sunction temperature		TSTG	-40		+125	°C
Junction temperature		Tj			+125	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	IF = 100 mA DC	VF			0.44	V
Reverse current	VR = 30V	IR			30	uA
Capacitance between terimnals	F = 1 MHZ and 10 VDC reverse voltage	CT		9		pF

RATING AND CHARACTERISTIC CURVES (CDBF0130)

Fig. 1 - Forward characteristics

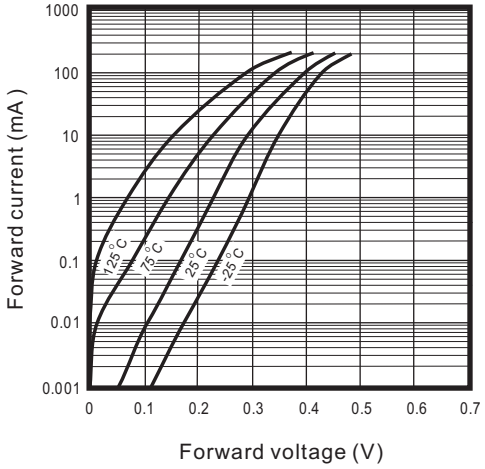


Fig. 2 - Reverse characteristics

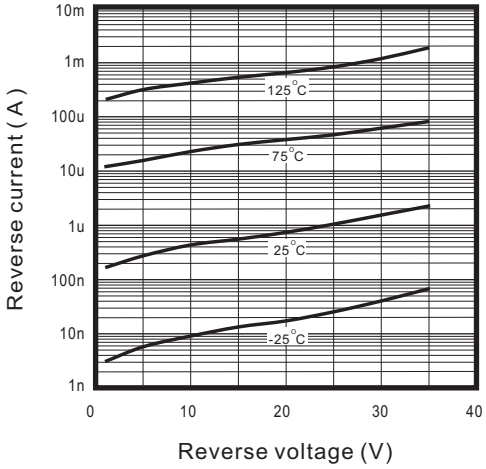


Fig.3 - Capacitance between terminals characteristics

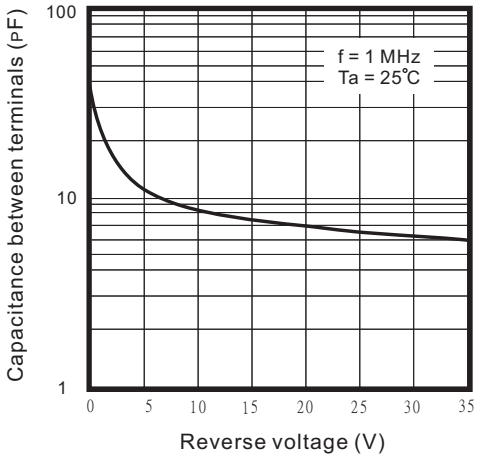


Fig.4 - Current derating curve